

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
2 May 2008 (02.05.2008)

PCT

(10) International Publication Number
WO 2008/049790 A1

(51) International Patent Classification:

C07F 17/00 (2006.01) C23C 16/30 (2006.01)

(21) International Application Number:

PCT/EP2007/061216

(22) International Filing Date: 19 October 2007 (19.10.2007)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

06301090.4 26 October 2006 (26.10.2006) EP

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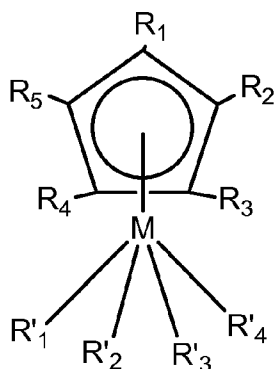
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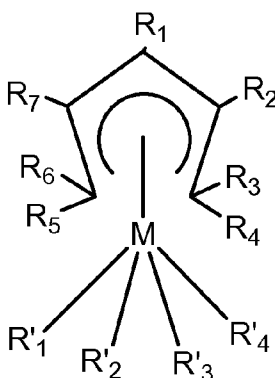
(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

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(54) Title: NEW GROUP V METAL CONTAINING PRECURSORS AND THEIR USE FOR METAL CONTAINING FILM DEPOSITION



(Ia)



(Ib)

(57) Abstract: Compound of the formula (Ia), or of the formula (Ib). These new precursors are useful for pure metal, metallic oxide, oxynitride, nitride and/or silicide film deposition to make electrodes and/or high k layers, and/or copper diffusion barrier layers, etc...



(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL,

PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*